

Device Modeling Report

COMPONENTS: BRT
PART NUMBER: RN1101FT
MANUFACTURER: TOSHIBA

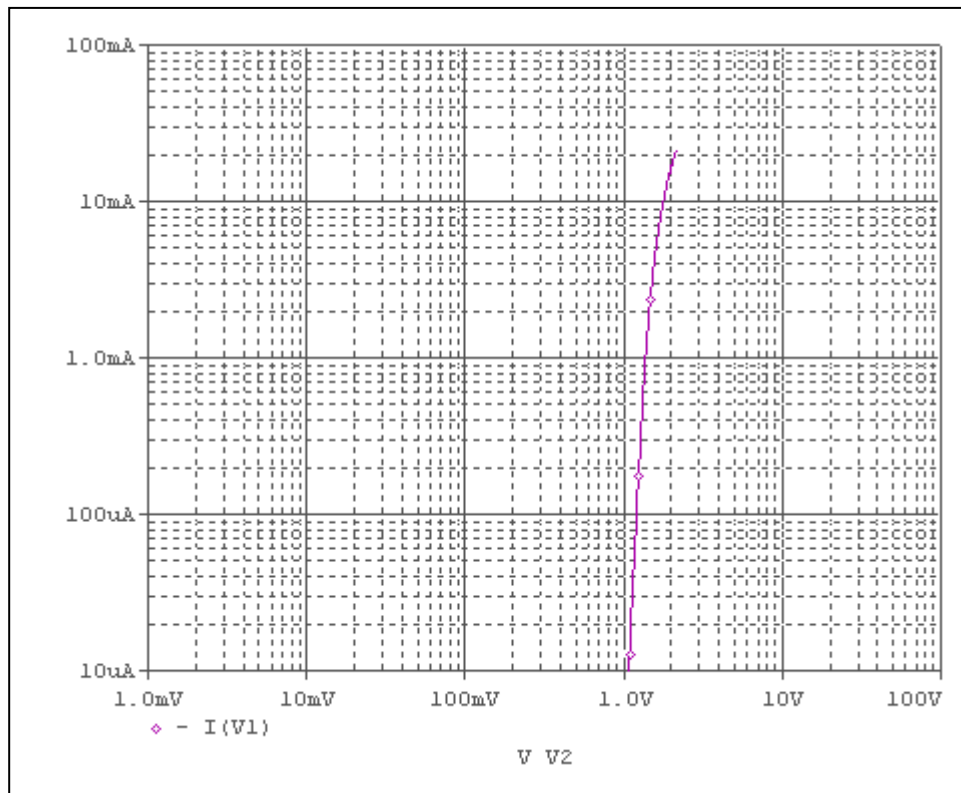


Bee Technologies Inc.

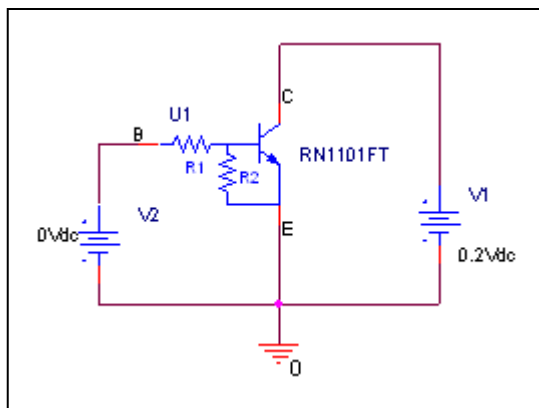
PSpice model parameter	Model description
IS	Saturation Current
BF	Ideal Maximum Forward Beta
NF	Forward Current Emission Coefficient
VAF	Forward Early Voltage
IKF	Forward Beta Roll-off Knee Current
ISE	Non-ideal Base-Emitter Diode Saturation Current
NE	Non-ideal Base-Emitter Diode Emission Coefficient
BR	Ideal Maximum Reverse Beta
NR	Reverse Emission Coefficient
VAR	Reverse Early Voltage
IKR	Reverse Beta Roll-off Knee Current
ISC	Non-ideal Base-Collector Diode Saturation Current
NC	Non-ideal Base-Collector Diode Emission Coefficient
NK	Forward Beta Roll-off Slope Exponent
RE	Emitter Resistance
RB	Base Resistance
RC	Series Collector Resistance
CJE	Zero-bias Emitter-Base Junction Capacitance
VJE	Emitter-Base Junction Potential
MJE	Emitter-Base Junction Grading Coefficient
CJC	Zero-bias Collector-Base Junction Capacitance
VJC	Collector-base Junction Potential
MJC	Collector-base Junction Grading Coefficient
FC	Coefficient for Onset of Forward-bias Depletion Capacitance
TF	Forward Transit Time
XTF	Coefficient for TF Dependency on Vce
VTF	Voltage for TF Dependency on Vce
ITF	Current for TF Dependency on Ic
PTF	Excess Phase at $f=1/2\pi \cdot TF$
TR	Reverse Transit Time
EG	Activation Energy
XTB	Forward Beta Temperature Coefficient
XTI	Temperature Coefficient for IS

Input voltage vs. output current (ON characteristics)

Circuit simulation result

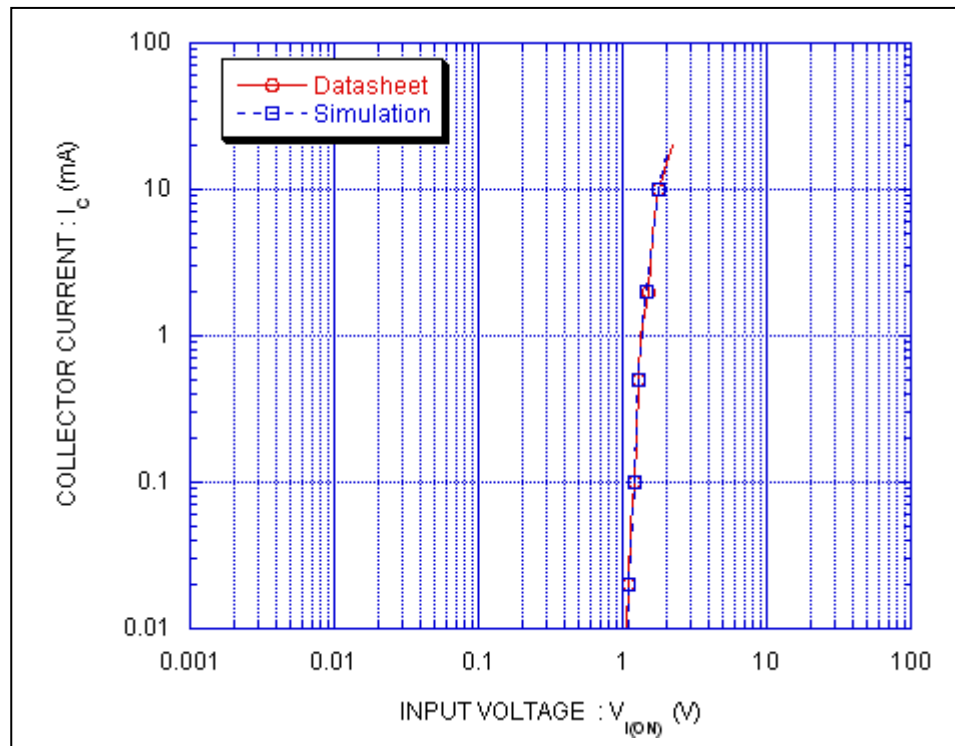


Evaluation circuit



Comparison Graph

Circuit Simulation Result



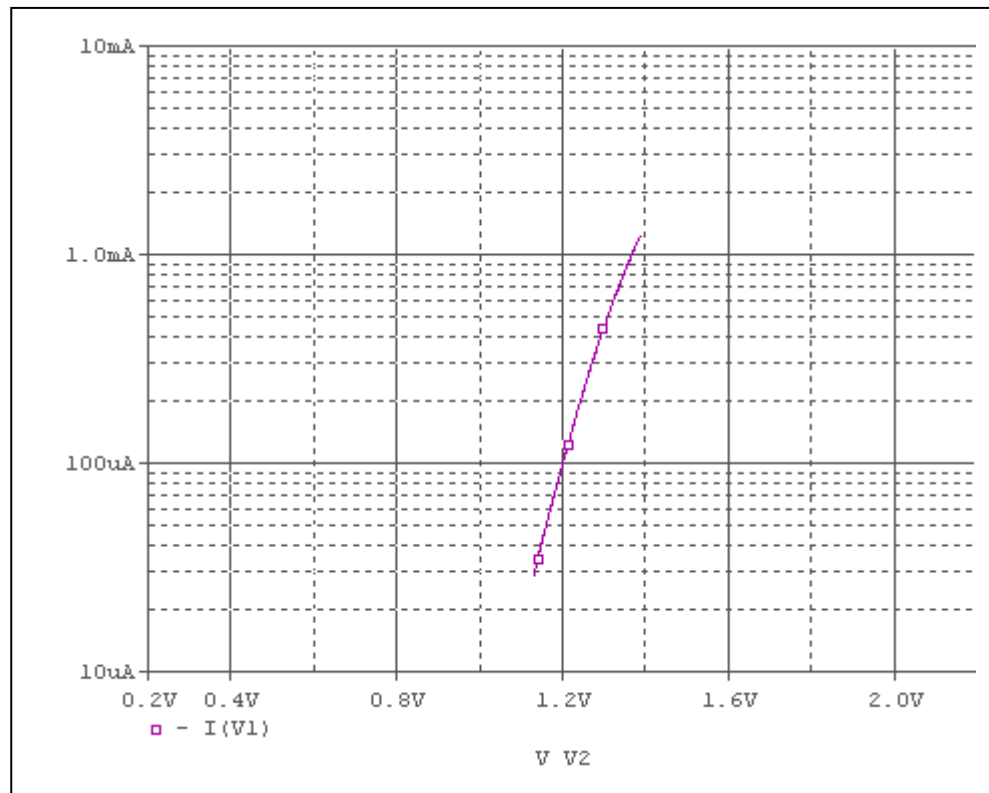
Simulation Result

Condition @ $V_{ce} = 0.2 \text{ V}$

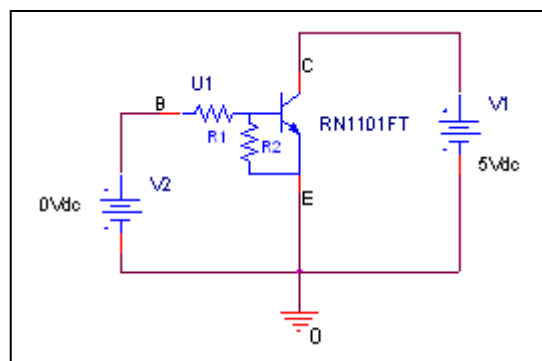
$I_c(\text{mA})$	$V_{I(\text{ON})} (\text{V})$		Error (%)
	Datasheet	Simulation	
0.01	1.05	1.0746	2.3429
0.02	1.1	1.1127	1.1545
0.05	1.15	1.1639	1.2087
0.1	1.20	1.2036	0.3000
0.2	1.25	1.2491	-0.0720
0.5	1.3	1.3135	1.0385
1	1.35	1.3725	1.6667
2	1.5	1.4497	3.3533
5	1.6	1.5971	0.1813
10	1.8	1.7841	0.8833
20	2.2	2.1121	3.9955

Output current vs. input voltage (OFF characteristics)

Circuit simulation result

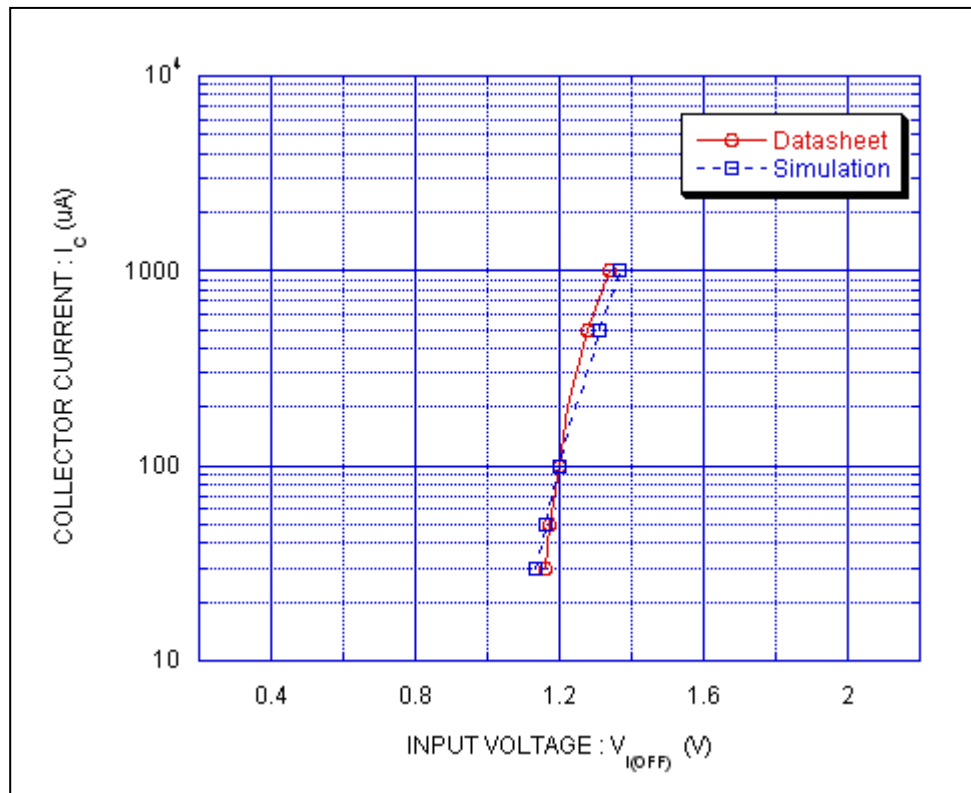


Evaluation circuit



Comparison Graph

Circuit Simulation Result



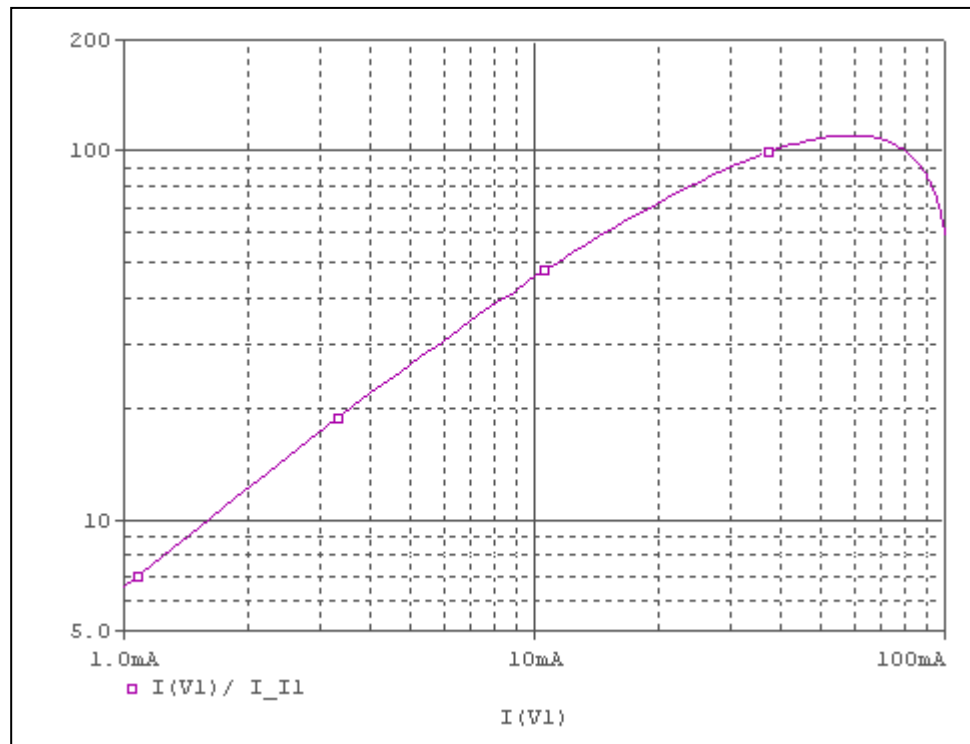
Simulation Result

Condition @ $V_{ce} = 5\text{ V}$

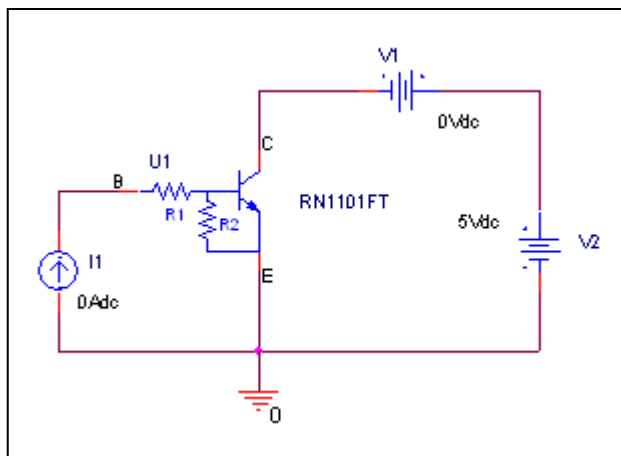
$I_c(\mu\text{A})$	$V_{I(Off)} (\text{V})$		Error (%)
	Datasheet	Simulation	
30	1.16	1.1327	-2.3534
50	1.17	1.1605	-0.8120
100	1.2	1.2007	0.0583
200	1.22	1.2448	2.0328
500	1.28	1.3086	2.2344
1000	1.34	1.3674	2.0448

DC current gain vs. output current

Circuit simulation result

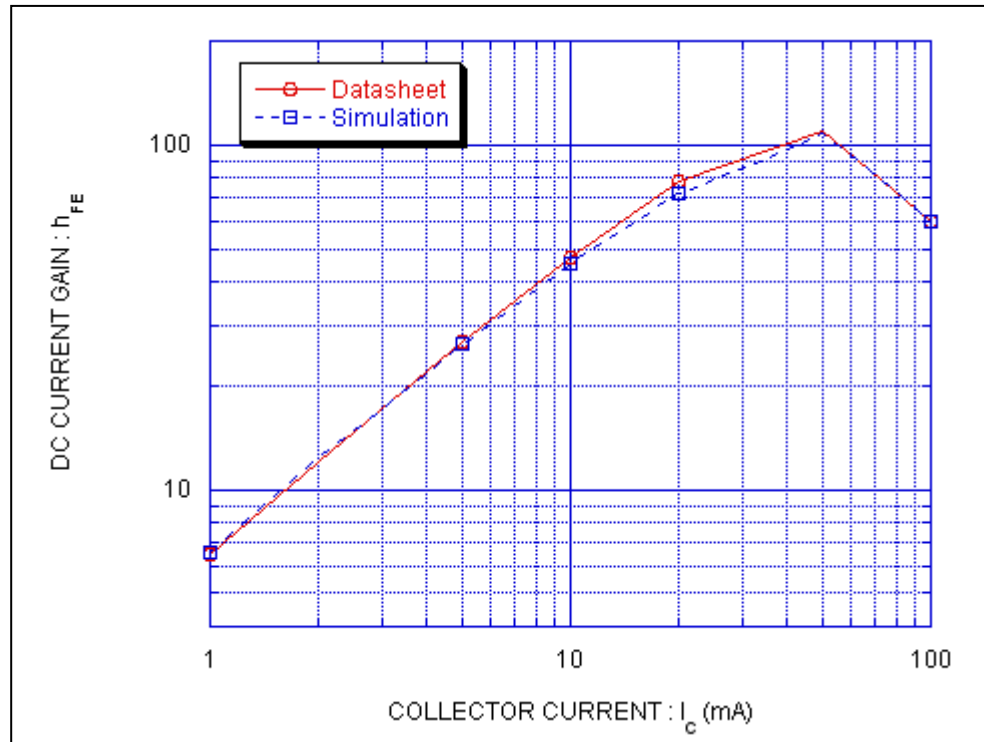


Evaluation circuit



Comparison Graph

Circuit Simulation Result



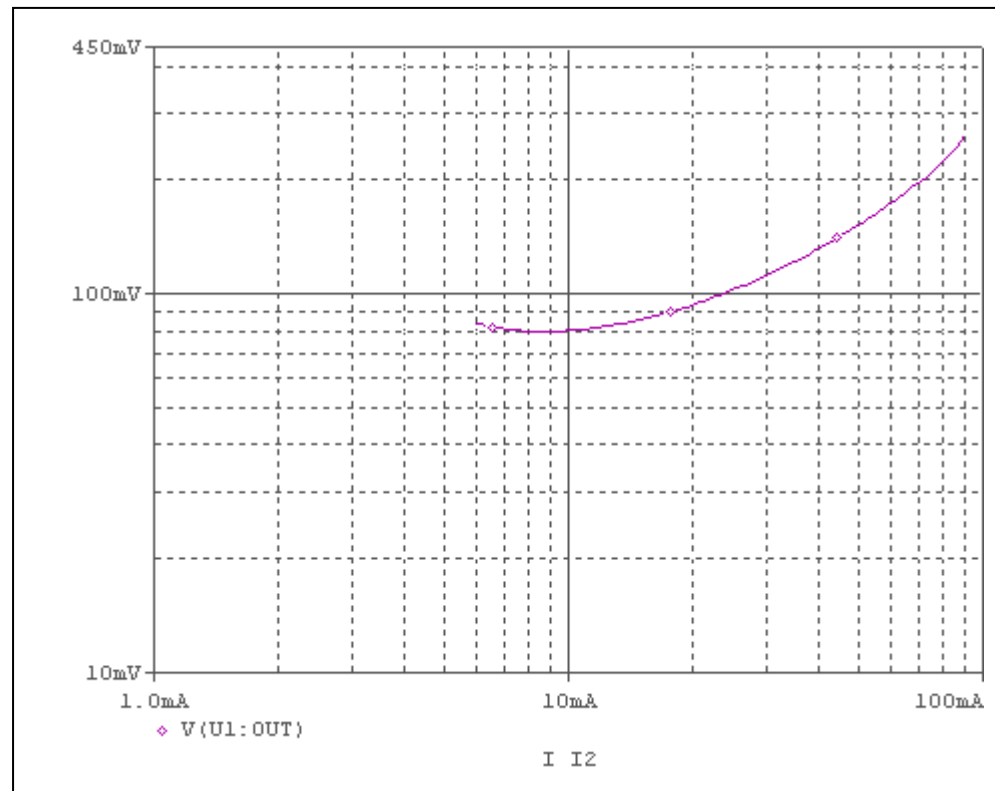
Simulation Result

Condition @ $V_{ce} = 5\text{ V}$

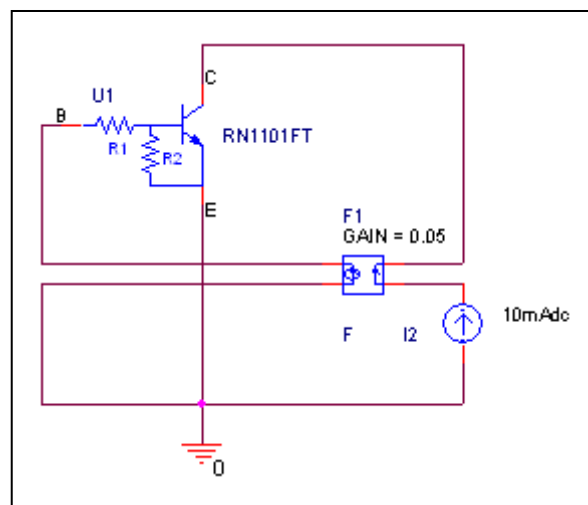
$I_C(\text{mA})$	hFE		Error (%)
	Datasheet	Simulation	
1	6.5	6.5896	1.3785
2	12	12.261	2.1750
5	27	26.554	-1.6519
10	47	45.356	-3.4979
20	78	72.503	-7.0474
50	110	108.449	-1.4100
100	60	59.947	-0.0883

Output voltage VS. output current

Circuit simulation result

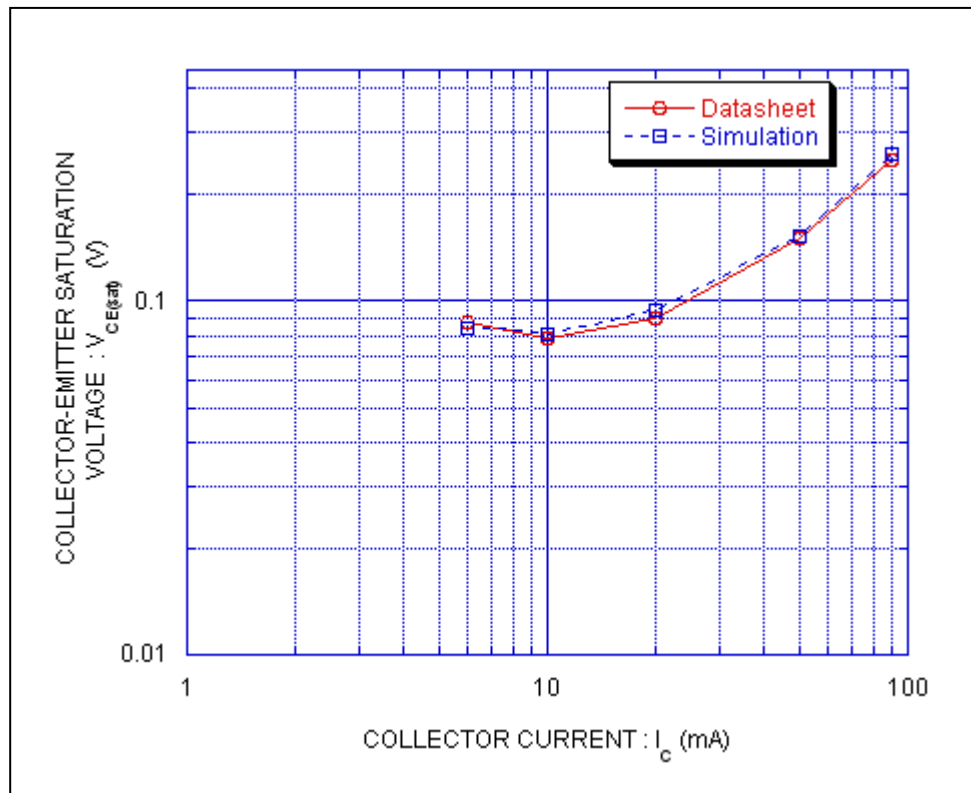


Evaluation circuit



Comparison Graph

Circuit Simulation Result



Simulation Result

Condition @ $I_C/I_B = 20$

Ic(mA)	V _{CE} (sat) (mV)		Error (%)
	Datasheet	Simulation	
6	0.087	0.083726	-3.7632
10	0.079	0.080103	1.3962
20	0.09	0.093702	4.1133
50	0.15	0.152472	1.6480
90	0.25	0.260047	4.0188